



**DDR2/3 multiphase power supply with multistate
phase-shedding to maximize energy savings**

Introduction

The worldwide trend in the computing industry is energy savings. In this sector, the focus is shifting from speed to performance per watt. STMicroelectronics is very sensitive to this trend, anticipating it, and being among the first silicon vendors to produce energy-saving devices according to Intel and AMD specifications. Today, thanks to a complete silicon portfolio, ST is able to offer an application for DDR2/3 memory power supply, with the highest efficiency over the whole range of current. The application is based on ST's L6756D Intel VR11.1 controller, with proprietary phase-shedding technology. The main feature of the application is the ability to automatically and dynamically change the number of phases (one, two, or four), based on the output current which allows saving switching losses when some phases are not needed. The energy savings is significant and can be up to four watts at light load and depending on application details, compared to standard power supply solutions. The size of such a design is small, making it suitable for both VRM and VRD solutions. The flexibility of the controller allows easily implementing a voltage regulator that can switch at one phase or two, one phase or three, or one phase or four. Three-state designs are also possible: one, two and three phases, according to the load; one, two and four phases, according to the load (multistate phase-shedding).

Contents

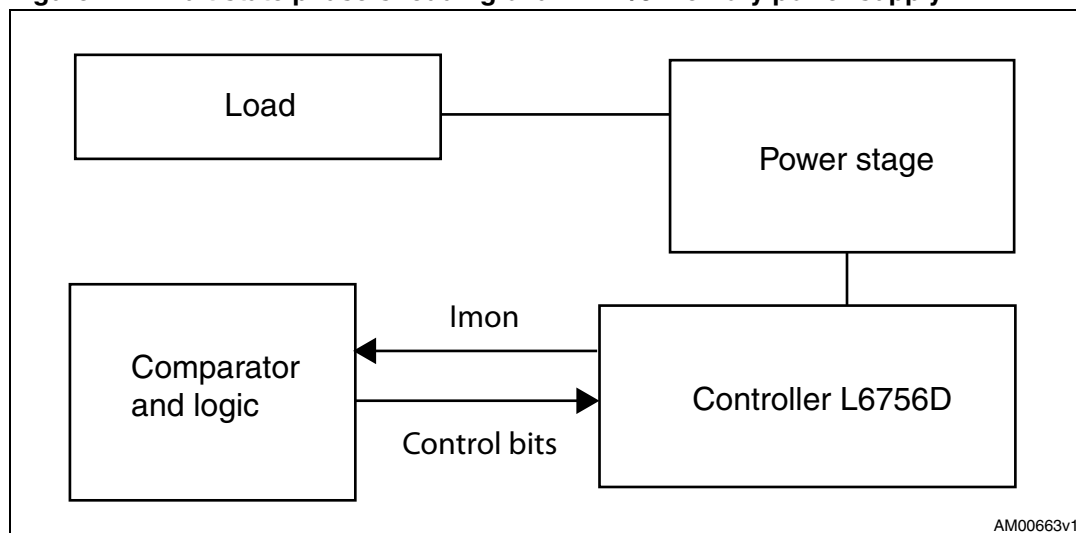
1	Operating principle	3
2	Efficiency boost	4
3	Additional features	5
4	References	5
5	Revision history	5

1 Operating principle

The operating principle of the DDR2/3 memory power supply with efficiency boost is based on the two input control pins (PSI, PSI_A) of the ST L6756D controller and on the output IMON pin of the L6756D. The IMON output pin voltage is proportional to the output current according to Intel VR11.1 specifications. The PSI and PSI_A input pins allow multiple states of power savings (multistate phase-shedding).

The load condition is automatically monitored by the controller, represented by IMON, and fed to the input pin of two comparators with programmable references. The phase number is changed by acting on the PSI and PSI_A pins (based on the IMON pin value). The output of the comparators drives the PSI pin and PSI_A pin respectively. The user has the freedom to adjust load threshold and hysteresis by changing the external resistor partitions. Overall, the external component count is small, with minimal impact on size. *Figure 1* illustrates multistate phase-shedding.

Figure 1. Multistate phase-shedding of a DDR2/3 memory power supply (a)



a. This solution leads to maximizing power savings over the whole current range, especially at light load.

2 Efficiency boost

The breakthrough of a phase-shedding solution, compared to designs with a fixed number of phases, is the possibility of saving energy at light loads. Of course the amount of energy and watts saved depends on the application details. However, on a standard DDR3 memory, the efficiency increase at light load has been measured to be in the range of 10% up to even 25% if the load is small which means up to 3.8 watts saved at a very light load. *Figure 2* illustrates these details. The red line is the efficiency measured with ST’s multistate phase-shedding application, whereas the blue line is the efficiency measured in a similar condition with a fixed-phase application. It is also very important to remark that usually PCs spend most of their time in idle mode, so it is very likely that the memory stays in low-consumption mode for a long time, leading to considerable energy savings if it is supplied with a phase-shedding application. ST’s L6756D, with its very flexible multistate phase-shedding, allows not only energy savings at light load, but also at medium load. As can be understood from *Figure 2*, the L6756D is running up to 18 A at one phase, from 18 A to 27 A at two phases, and from current values higher than 27 A at four phases.

Figure 2. Efficiency measurement of a power supply for a DDR3 memory (b)

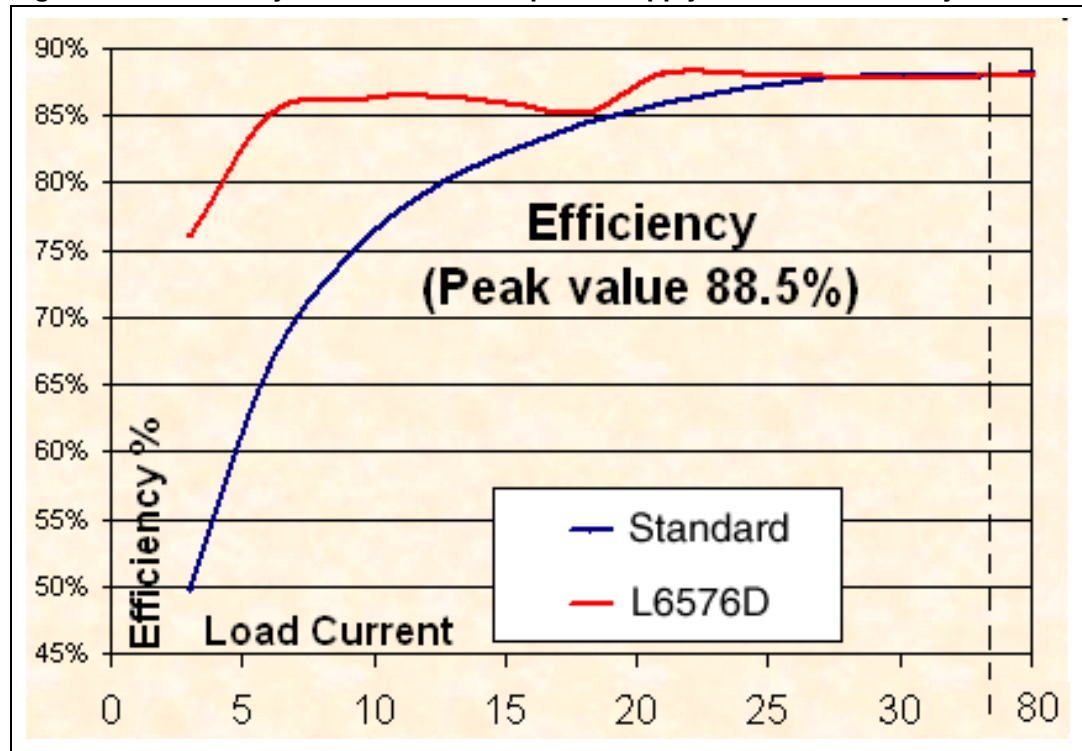


Figure 2 depicts a representation of one specific case. The current thresholds, as well as hysteresis values, can be easily changed.

b. A multistate phase-shedding vs. a fixed-phase power supply. The first method results in considerable energy savings.

3 Additional features

The solution described in this article also has many other very interesting features. Soft-start is always performed at full load, in order to be compatible with any load. After the soft-start is finished, the controller uses the best number of phases. Phase shift among phases is always optimized at 90° at four phases, 120° at three phases, and 180° at two phases. The voltage regulation of the controller is outstanding. Whatever the number of phases, the voltage ripple is small and almost constant, and transient performance matches the application expectations.

4 References

1. STMicroelectronics L6756D datasheet

5 Revision history

Table 1. Revision history

Date	Revision	Changes
09-Sep-2008	1	First issue

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